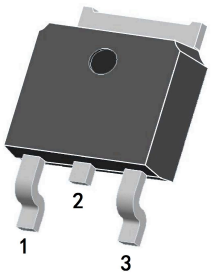
20V N-Channel Mosfet

FEATURES

- RDS(ON) < 6mΩ @ VGS = 4.5V
- RDS(ON) < 8.8mΩ @ VGS = 2.5V

TO-252

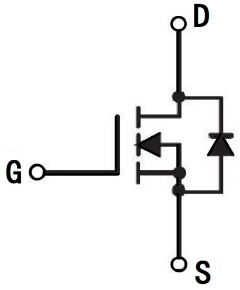


1: G
2: D
3: S

APPLICATIONS

- Load Switch
- PWM Application
- Power management

N-CHANNEL MOSFET



MAXIMUM RATINGS (TC=25°C unless otherwise noted)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25℃	60	A
		T_C = 100℃	39	A
I_{DM}	Pulsed Drain Current note1		240	A
E_{AS}	Single Pulsed Avalanche Energy note2		120	mJ
P_D	Power Dissipation	T_C = 25℃	34	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.4	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

ELECTRICAL CHARACTERISTICS TJ=25 °C unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.4	0.65	1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=4.5V, I_D=20A	-	4.6	6.0	mΩ
		V_{GS}=2.5V, I_D=15A	-	6.2	8.8	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1.0MHz	-	1935	-	pF
C_{oss}	Output Capacitance		-	478	-	pF
C_{rss}	Reverse Transfer Capacitance		-	194	-	pF
Q_g	Total Gate Charge	V_{DS}=10V, I_D=20A, V_{GS}=4.5V	-	27	-	nC
Q_{gs}	Gate-Source Charge		-	6.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	6.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V, I_D=2A, R_{GEN}=3Ω, V_{GS}= 4.5V	-	6	-	ns
t_r	Turn-on Rise Time		-	17	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	28	-	ns
t_f	Turn-off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	60	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	240	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time		-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge	IF=20A, dI/dt=100A/μs	-	20	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=10V, V_G=4.5V, L=0.5mH, R_G=25Ω, I_{AS}=22A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

TYPICAL CHARACTERISTICS

Figure1: Output Characteristics

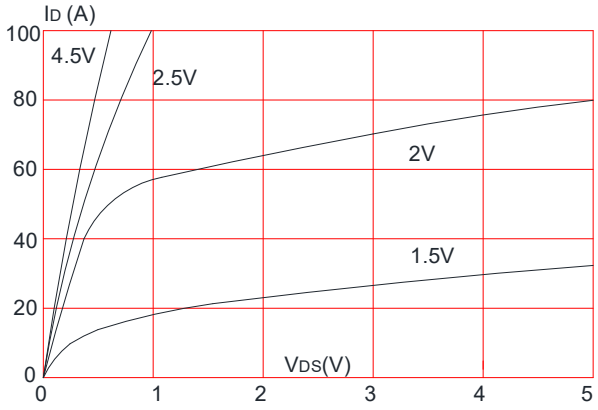


Figure 2: Typical Transfer Characteristics

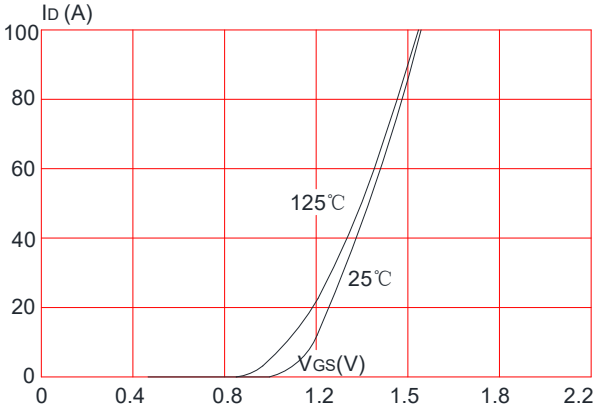


Figure 3: On-resistance vs. Drain Current

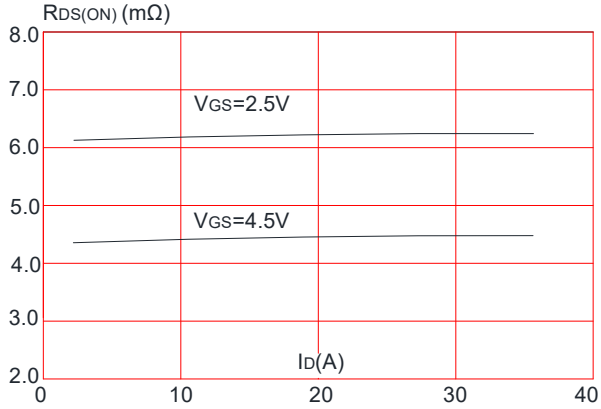


Figure 4: Body Diode Characteristics

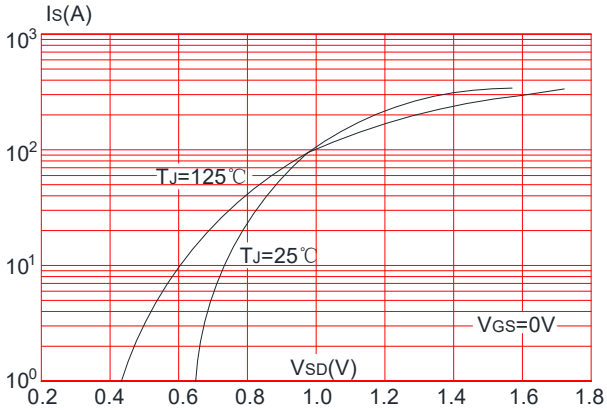


Figure 5: Gate Charge Characteristics

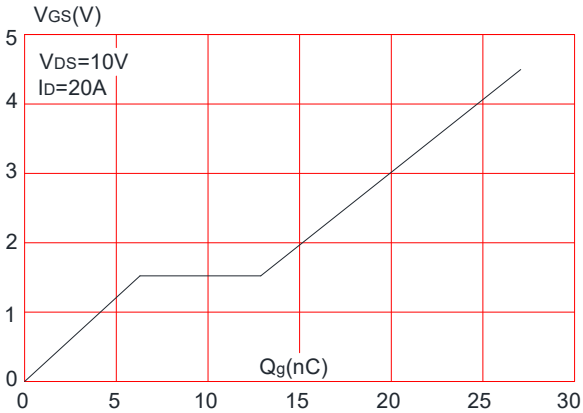
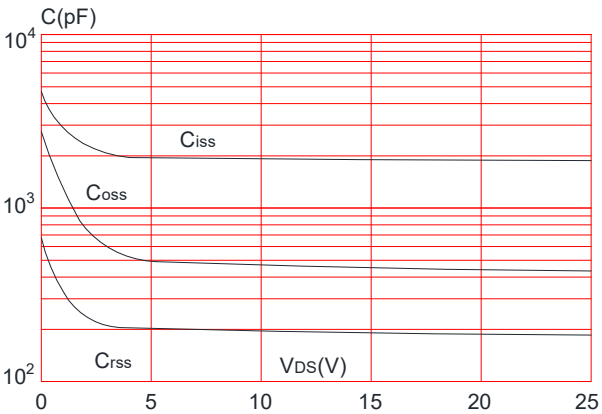


Figure 6: Capacitance Characteristics



TYPICAL CHARACTERISTICS (cont.)

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

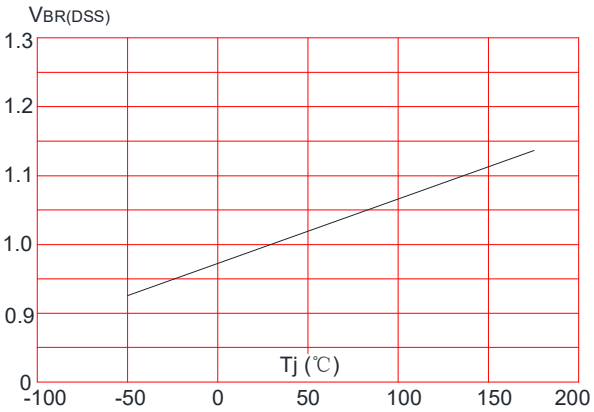


Figure 8: Normalized on Resistance vs. Junction Temperature

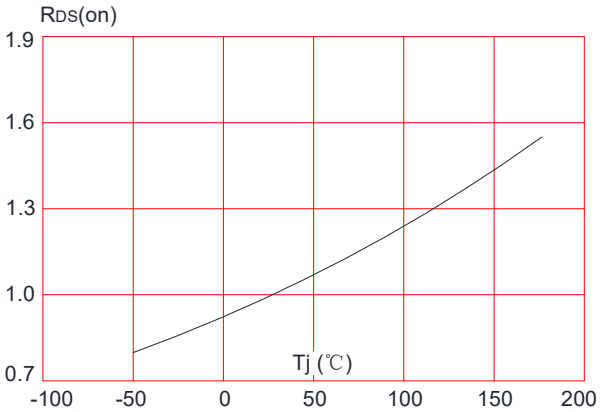


Figure 9: Maximum Safe Operating Area

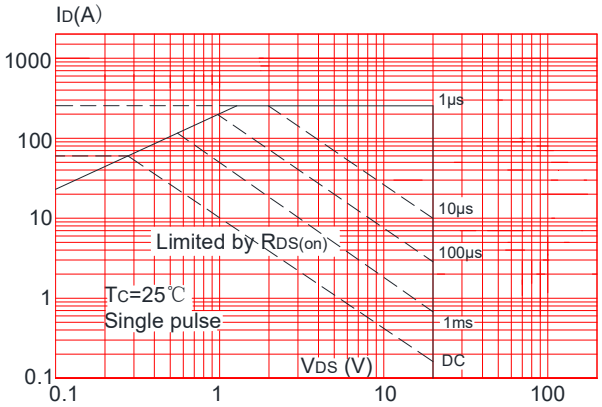


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

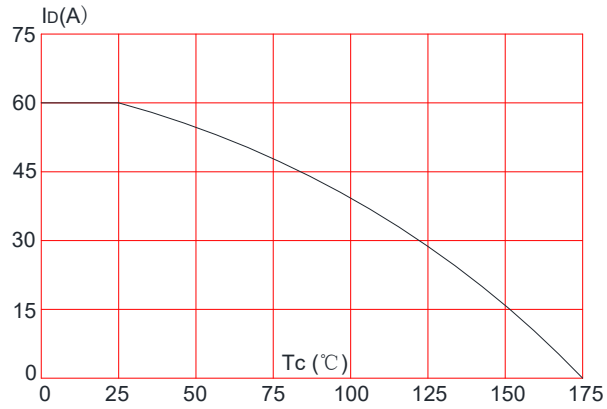
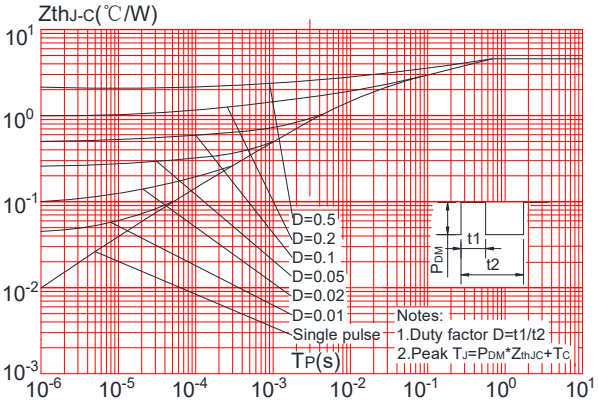
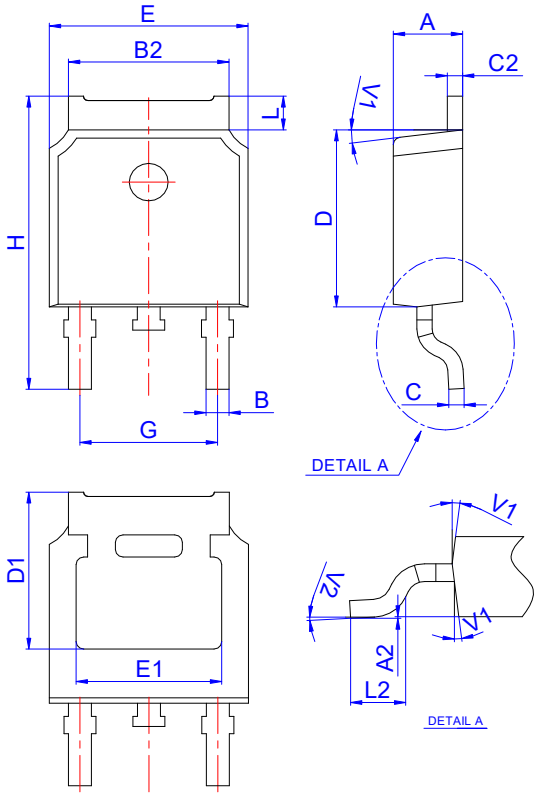


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



TO-252 PACKAGE OUTLINE DRAWING



Symbols	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°